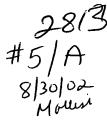


## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re the Application of: •

YASUMOTO, Tamihide

Group Art Unit: 2813

Serial No.: 09/995,575

Examiner: KIELIN, E.

Filed: November 29, 2001

P.T.O. Confirmation No.: 1497

· For:

SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING

## **AMENDMENT**

Commissioner for Patents Washington, D.C. 20231

August 20, 2002

Sir:

In response to the Office Action dated June 5, 2002, please amend the above-identified application

as follows:

IN THE ABSTRACT:

Please delete the current Abstract and replace therewith the attached substitute Abstract.

AUG 23 2002

## IN THE SPECIFICATION:

Please replace the paragraph at page 2, lines 13-23 with the following rewritten paragraph:

According to one aspect of the present invention, there is provided a method for manufacturing a semiconductor device, comprising the steps of: forming a wiring comprising silicon on a surface of a semiconductor substrate; covering part of the wiring with a resist pattern; implanting ions into the wiring